

isc Silicon NPN Darlington Power Transistor

2SD2102

DESCRIPTION

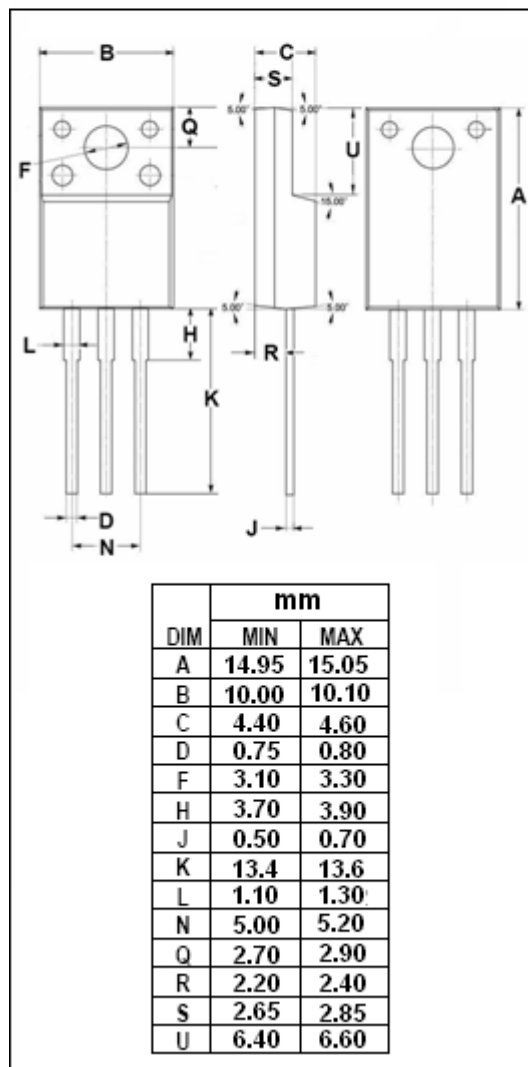
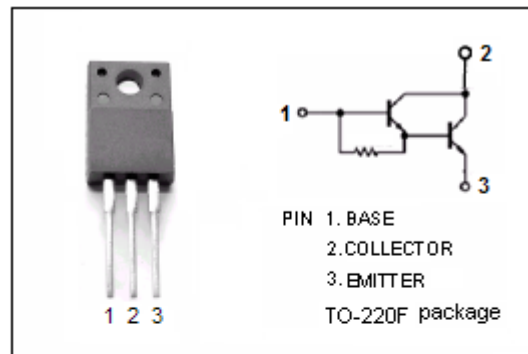
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 60V(\text{Min})$
- High DC Current Gain
: $h_{FE} = 1000(\text{Min}) @ I_C = 2A, V_{CE} = 3V$

APPLICATIONS

- Designed for low frequency power amplifier applications

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	4	A
I_{CM}	Base Current-Peak	8	A
P_C	Collector Power Dissipation @ $T_a = 25^\circ\text{C}$	2	W
	Collector Power Dissipation @ $T_c = 25^\circ\text{C}$	25	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon NPN Darlington Power Transistor**2SD2102****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 25mA ; R _{BE} = ∞	60			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 0.1mA; I _E = 0	60			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 50mA; I _C = 0	7			V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 2A; I _B = 4mA			1.5	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = 4A; I _B = 40mA			3.0	V
V _{BE(sat)-1}	Base-Emitter Saturation Voltage	I _C = 2A; I _B = 4mA			2.0	V
V _{BE(sat)-2}	Base-Emitter Saturation Voltage	I _C = 4A; I _B = 40mA			3.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 50V; I _E = 0			10	μ A
I _{CEO}	Collector Cutoff Current	V _{CE} = 50V; R _{BE} = ∞			10	μ A
h _{FE}	DC Current Gain	I _C = 2A ; V _{CE} = 3V	1000		20000	